

# Abstracts

## High Power GaAs IMPATT Amplifier (Dec. 1977 [T-MTT])

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*K. Nishitani, H. Sawano, T. Ishii, S. Mitsui, E. Kaji and A. Amano. "High Power GaAs IMPATT Amplifier (Dec. 1977 [T-MTT])." 1977 Transactions on Microwave Theory and Techniques 25.12 (Dec. 1977 [T-MTT] (1977 Symposium Issue)): 973-977.*

10-W p-n junction GaAs IMPATT diodes with MTTF more than  $10^6$  h, have been developed. Using these diodes, amplifiers of 5-W output power, 10-dB gain, 17-percent efficiency, 150-MHz bandwidth, and 80-dB signal-to-noise ratio (S/N ratio) have been constructed.

 [Return to main document.](#)